

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Nobuyuki SUGII et al.

Appln. No.:

Filed: Herewith

For: INSULATED-GATE FIELD-EFFECT TRANSISTOR, METHOD OF  
FABRICATING SAME, AND SEMICONDUCTOR DEVICE EMPLOYING  
THE SAME

\* \* \*

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any  
assertion as to materiality or prior art effect, the  
documents listed on the attached Form PTO-1449 are hereby  
cited.

The Japanese documents AJ-AM on the attached List are  
accompanied by English abstracts. Documents AJ-AL are also  
cited in the specification, on pages 2-5.

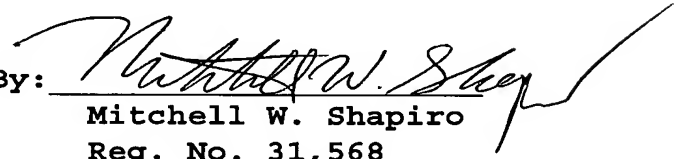
Documents AP and AQ are cited in the specification, on  
pages 2-4, and their relevance is indicated therein.

Respectfully submitted,

MWS:sjk

Miles & Stockbridge P.C.  
1751 Pinnacle Drive  
Suite 500  
McLean, Virginia 22102-3833  
(703) 903-9000

By:

  
Mitchell W. Shapiro  
Reg. No. 31,568

September 30, 2003

<b>FORM PTO-1449</b>				Atty. Docket No. <b>XA-9947</b>		Appln. No.	
<b><u>LIST OF DOCUMENTS CITED BY APPLICANT</u></b>				Applicant <b>Nobuyuki SUGII et al.</b>			
				Filing Date <b>HEREWITH</b>		Group	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	<b>6,563,152</b>	<b>05/13/03</b>	<b>Roberds et al.</b>	<b>257</b>	<b>288</b>	
	AB	<b>6,475,869</b>	<b>11/05/02</b>	<b>Yu</b>	<b>438</b>	<b>303</b>	
	AC	<b>6,403,981</b>	<b>06/11/02</b>	<b>Yu</b>	<b>257</b>	<b>63</b>	
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AJ	<b>2002-16255</b>	<b>01/18/02</b>	<b>Japan</b>			<b>Abstract</b>
	AK	<b>9-321307</b>	<b>12/12/97</b>	<b>Japan</b>			<b>Abstract</b>
	AL	<b>2000-286418</b>	<b>10/13/00</b>	<b>Japan</b>			<b>Abstract</b>
	AM	<b>2003-17710</b>	<b>01/17/03</b>	<b>Japan</b>			<b>Abstract</b>
	AN						
	AO						
<b>OTHER</b> (including author, title, date, pertinent pages, etc.)							
	AP	<b>Hisamoto et al., "A Folded-channel MOSFET for Deep-sub-tenth Micron Era," Proceedings of the International Electronic Device Conference (IEDM), 1988, pp. 1032-1034.</b>					
	AQ	<b>Nikkei Electronics, July 16, 2001, pp. 63-70.</b>					
	AR						
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							